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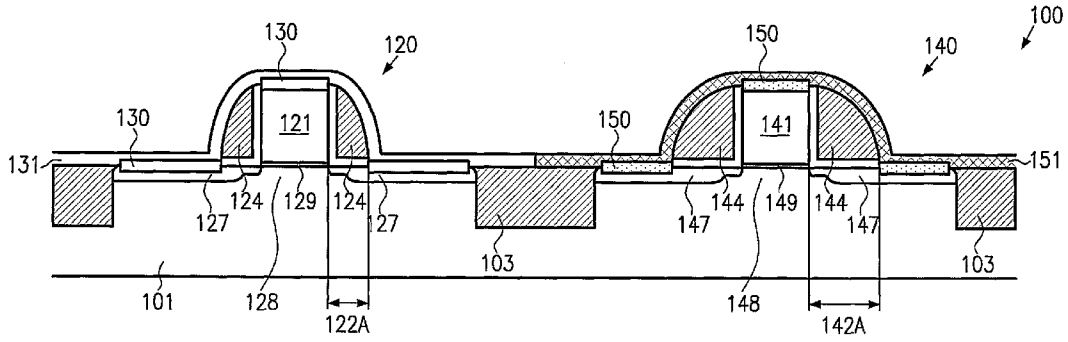
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(54) **Title:** TECHNIQUE FOR FORMING CONTACT INSULATION LAYERS SILICIDE REGIONS WITH DIFFERENT CHARACTERISTICS



(57) **Abstract:** A technique is provided that enables the formation of metal suicide individually for N-channel transistors and P-channel transistors, while at the same time a strain-inducing mechanism is also provided individually for each transistor type. In this way, a cobalt suicide (130, 230) having a reduced distance to the channel region of an NMOS transistor (120, 220) may be provided, while a P-channel transistor (140, 240) may receive a highly conductive nickel suicide (150, 250), without unduly affecting or compromising the characteristics of the N-channel transistor (120, 220).

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